

R-C Thermal Model Parameters

DESCRIPTION

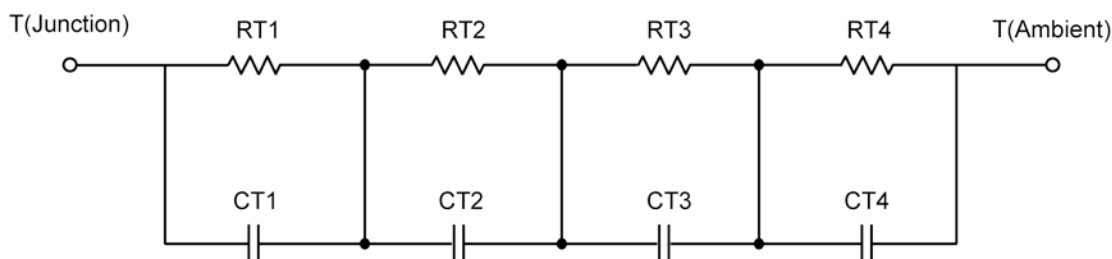
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	22.8642	N/A	15.7114
RT2	32.3160	N/A	11.1001
RT3	3.4885	N/A	2.7735
RT4	51.3313	N/A	7.4150
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	9.1663 m	N/A	128.4945 m
CT2	58.8820 m	N/A	8.0466 m
CT3	794.0542 u	N/A	573.1008 u
CT4	1.6539	N/A	30.7959 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	6.0654	N/A	3.3573
RF2	29.7470	N/A	18.7985
RF3	26.2871	N/A	11.8926
RF4	47.9005	N/A	2.9516
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	1.1556 m	N/A	512.9510 u
CF2	8.3486 m	N/A	6.0017 m
CF3	70.6858 m	N/A	112.4543 m
CF4	1.7500	N/A	272.1569 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

